

MD2009DFP

High voltage NPN power transistor for CRT TV

Features

- State-of-the-art technology:
 - diffused collector "enhanced generation"
- Stable performance versus operating temperature variation
- Low base drive requirement
- Tight h_{FE} range at operating collector current
- Fully isolated power package UL compliant
- Integrated free wheeling diode

Application

Horizontal deflection output for CRT TV

Description

The MD2009DFP is manufactured using diffused collector in planar technology adopting new and enhanced high voltage structure. The new MD product series show improved silicon efficiency bringing updated performance to the horizontal deflection stage.

Table 1. Device summary

Order code	Marking	Package	Packaging
MD2009DFP	MD2009DFP	TO-220FP	Tube



Figure 1. Internal schematic diagram



1 Electrical ratings

Table 2.	Absolute	maximum	ratings
	Absolute	maximum	raungs

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{BE} = 0$)	1500	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	700	۷
V_{EBO}	Base-emitter voltage ($I_C = 0$)	7	V
۱ _C	Collector current	10	А
I _{CM}	Collector peak current (t _P < 5ms)	16	А
Ι _Β	Base current	6	А
P _{TOT}	Total dissipation at $T_c = 25^{\circ}C$	40	W
V _{ISO} Isolation withstand voltage (RMS) from all t leads to external heatsink		2500	V
T _{stg}	Storage temperature -65 to 150		ŝ
Τ _J	Max. operating junction temperature	150	

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	3.12	°C/W

2 Electrical characteristics

(T_{case} =25°C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	V _{CE} = 1500V V _{CE} = 1500V, T _c = 125°C			0.2 2	mA mA
I _{EBO}	Emitter cut-off current $(I_{\rm C} = 0)$	V _{EB} = 5V	40		120	mA
V _{(BR)EBO}	Emitter-base breakdown voltage (I _C = 0)	I _E = 700mA	10			v
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	$I_{\rm C} = 5.5 {\rm A}$, $I_{\rm B} = 1.4 {\rm A}$			2.8	۷
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	$I_{\rm C} = 5.5 {\rm A}$, $I_{\rm B} = 1.4 {\rm A}$			1.3	۷
h _{FE} ⁽¹⁾	DC current gain	$ \begin{array}{ll} I_{C} = 1 A, & V_{CE} = 5 V \\ I_{C} = 5.5 A, & V_{CE} = 1 V \\ I_{C} = 5.5 A , & V_{CE} = 5 V \end{array} $	5	18 4.7	7	
$V_{F}^{(1)}$	Diode forward voltage	I _F = 5.5 A			1.6	V
t _s t _f	Inductive load Storage time Fall time	$\begin{split} I_C &= 5\text{A}, \ \ f_h = 16\text{KHz} \\ I_{B(on)} &= 1.5\text{A}, \ \ V_{BE(off)} = -2.7\text{V} \\ I_{BB(off)} &= 6.2\mu\text{H} \end{split}$		4.5 0.3	6 0.6	μs μs

Table 4. Electrical characteristics

1. Pulse test: pulse duration \leq 300 µs, duty cycle \leq 2%.



DG11570

Is∕₿

100 125 T_{case}(°C)

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area







Figure 3.

P_{tot} (%)

100

80

60

40

20

0

Figure 5.

25 50 75

Reverse biased SOA

Derating curve









MD2009DFP

Figure 8. Collector-emitter saturation voltage Figure 9. Base-emitter saturation voltage



Figure 10. Power losses

Figure 11. Inductive load switching time





3 Test circuits



Figure 12. Power losses and inductive load switching test circuit







4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.



TU-ZZUFP mechanical data	TO-220FP	mechanical	data
--------------------------	----------	------------	------

Dim	mm		
Dim.	Min.	Тур.	Max.
A	4.4		4.6
В	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
н	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



Doc ID 16108 Rev 1



5 Revision history

Table 5.Document revision history

Date	Revision	Changes
11-Aug-2009	1	First release



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2009 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

Doc ID 16108 Rev 1



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by STMicroelectronics manufacturer:

Other Similar products are found below :

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B